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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	Fusao Ishii	:	Date: September 12, 2008
Serial No.:	10/698,620	:	Group No.: 2873
Filed:	November 1, 2003	:	Examiner: Brandi N. Thomas
Attorney Docket No.:	FIshii001	:	@(571)272-2341(T)872-9306(F)

CERTIFICATION UNDER 37 CFR 1.10

I hereby certify that this Office Response Transmittal and the documents referred to as enclosed therein are being deposited with the United States Postal Service on this date **September 12, 2008** in an envelope as "Express Mail Post Office to Addressee" Mailing Label Number **EB887275246 US"** addressed to the: Commissioner of Patents and Trademarks, Alexandria, VA. 22313-1450.

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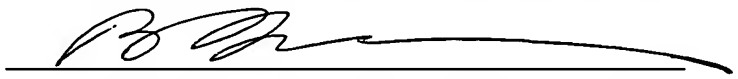

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To the Commissioner of Patents and Trademarks:

AMENDMENT

Dear Sir:

In response to the Examiner's Action mailed on May 12, 2008, the Applicant hereby respectfully requests a one months extension with an extension fee of $60 enclosed. Please amend the above referenced Patent Application be amended as set forth below.

I) Please amend claims 1 to 60 as set forth below:

September 12, 2008

1. (Currently Amended) An electromechanical micromirror device, comprising:

a single semiconductor substrate with a bottom surface and a top surface opposite said bottom surface;

a control circuitry disposed on said bottom surface of said single substrate; and

a micromirror section disposed on said top surface of said single semiconductor substrate;

wherein said micromirror section comprises a micromirror; and

at least one support structure for supporting said micromirror and via connectors opened through said single semiconductor substrate for connecting said control circuit to said support structure.

2. (Currently Amended) 2. The device of claim 1, wherein:

said control circuitry disposed on said bottom surface of said single semiconductor substrate comprising a circuit selected from the group consisting of: CMOS circuits, NMOS circuits, PMOS circuits, bipolar circuits, BiCMOS circuits, DMOS circuits, HEMT circuits, amorphous silicon thin film transistor circuits, polysilicon thin film transistor circuits, SiGe transistor circuits, SiC transistor circuits, GaN transistor circuits, GaAs transistor circuits, InP transistor circuits, CdSe transistor circuits, organic transistor circuits, and conjugated polymer transistor circuits.